

Nano Current Power I_QSmart[™] Switch with True Reverse Current Blocking

Product Specification

DESCRIPTION

The GLF1200H / GLF1201H is an advanced technology fully integrated I_QSmart^{TM} load switch device with True Reverse Current Blocking (TRCB) technology and the slew rate control of the output voltage.

The GLF1200H / GLF1201H offers industry leading True Reverse Current Blocking (TRCB) performance, featuring an ultra-low threshold voltage. It minimizes reverse current flow in the event that the VOUT pin voltage exceeds the VIN voltage.

An integrated slew rate control can also enhance system reliability by mitigating bus voltage swings during switching events. Where uncontrolled switches can generate high inrush currents that result in voltage droop and/or bus reset events, the GLF slew rate control specifically limits inrush currents during turn-on to minimize voltage droop.

The GLF1200H / GLF1201H load switch device supports an industry leading wide input voltage range and helps to improve operating life and system robustness. Furthermore, one device can be used in multiple voltage rail applications which helps to simplify inventory management and reduces operating cost.

FEATURES

True Reverse Current Blocking

• Ultra-Low I_Q : 0.47 μ A Typ at 5.5 V_{IN} • Ultra-Low I_{SD} : 26 nA Typ at 5.5 V_{IN} • Low R_{ON} : 54 m Ω Typ at 5.5 V_{IN}

• Іоит Мах: 2 A

Wide Input Range: 1.5 V to 5.5 V

6 V abs max

• Controlled Rise Time: 600 µs at 3.3V_{IN}

• Internal EN Pull-Down Resistor on

 Integrated Output Discharge Switch: GLF1201H

Wide Operating Temperature Range:

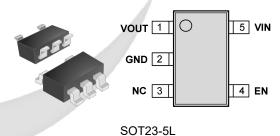
-40 °C ~ 105 °C

HBM: 4 kV, CDM: 2 kV

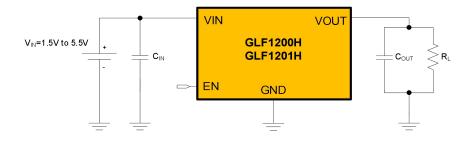
APPLICATIONS

- Smart IoT Devices
- Portable Industrial Devices
- Low Power Subsystems

PACKAGE



APPLICATION DIAGRAM



GLF1200H, GLF1201H Nano Current Power I_QSmart[™] Switch with TRCB

ALTERNATE DEVICE OPTIONS

Part Number	Top Mark	R _{on} (Typ) at 5.5 V _{IN}	TRCB	Output Discharge	EN Activity
GLF1200H-T1G7	DMH	54 mΩ	Yes	NA	High
GLF1201H-T1G7	DNH	54 mΩ	res	85 Ω	High

FUNCTIONAL BLOCK DIAGRAM

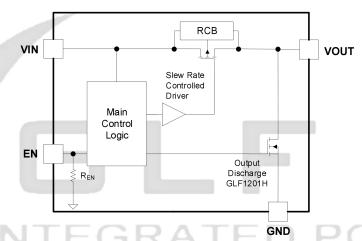


Figure 1. Functional Block Diagram

PIN CONFIGURATION

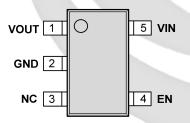


Figure 2. SOT23-5L

PIN DEFINITION

Pin#	Name	Description
1	VOUT	Switch Output
2	GND	Ground
3	NC	No connection
4	EN	Enable to control the switch
5	VIN	Switch Input. Supply Voltage for IC

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ABSOLUTE MAXIMUM RATINGS

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions; extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Pai	Min.	Max.	Unit	
V _{IN}	VIN, VOUT, VEN to GND	V _{IN} , V _{OUT} , V _{EN} to GND			
lout	Maximum Continuous Switch Current			2	Α
T _{STG}	Storage Junction Temperature	-65	150	°C	
θ _{JC}	Thermal Resistance, Junction to Case		90	°C/W	
θ_{JA}	Thermal Resistance, Junction to Ambient			180	°C/W
ECD	Floatroatatia Disabarra Canability	Human Body Model, JESD22-A114	4		14/
ESD	Electrostatic Discharge Capability	Charged Device Model, JESD22-C101	2		kV

Note. The θ_{JA} is measured at $T_A = 25^{\circ}$ C on a high effective thermal conductivity four-layer test board per JEDEC 51-7.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Max.	Unit
V _{IN}	Supply Voltage	1.5	5.5	V
T _A	Ambient Operating Temperature	-40	+105	°C

ELECTRICAL CHARACTERISTICS

Values are at V_{IN} = 3.3V and T_A = 25°C unless otherwise noted.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit		
Basic Ope	eration							
1		V _{IN} = V _{EN} = 5.5 V, I _{OUT} = 0 mA			0.47			
IQ	Quiescent Current (1)	$V_{IN} = V_{EN} = 5.5 \text{ V}, I_{OUT} = 0 \text{ mA},$	$T_A = 85 ^{\circ}C^{(4)}$		0.52		μA	
		$V_{IN} = V_{EN} = 5.5 \text{ V}, I_{OUT} = 0 \text{ mA},$	$T_A = 105 ^{\circ}C^{(4)}$,	0.54			
		$V_{EN} = 0 \text{ V}, V_{IN} = 1.5 \text{ V } I_{OUT} = 0$	mA		2.0			
		$V_{EN} = 0 \text{ V}, V_{IN} = 3.3 \text{ V } I_{OUT} = 0$	mA		3.0			
I _{SD}	Shut Down Current	$V_{EN} = 0 \text{ V}, V_{IN} = 4.2 \text{ V } I_{OUT} = 0$	mA		10		1	
ISD	Shut Down Current	V _{EN} = 0 V, V _{IN} = 5.5 V I _{OUT} = 0 mA			26		nA	
		$V_{EN} = 0 \text{ V}, V_{IN} = 5.5 \text{ V}, I_{OUT} = 0 \text{ mA}, T_A = 85 °C (4)$			365			
		$V_{EN} = 0 \text{ V}, V_{IN} = 5.5 \text{ V}, I_{OUT} = 0 \text{ mA}, T_A = 105 °C (4)$			1020			
			T _A = 25 °C		54			
		$V_{IN} = 5.5 \text{ V}, I_{OUT} = 500 \text{ mA}$	T _A = 85 °C ⁽⁴⁾		63			
			T _A = 105 °C ⁽⁴⁾		68		mΩ	
Ron	On-Resistance		T _A = 25 °C		64			
TON	On-redistance	V _{IN} = 3.3 V, I _{OUT} = 500 mA	T _A = 85 °C ⁽⁴⁾		75		111152	
			T _A = 105 °C ⁽⁴⁾		81			
		V_{IN} = 1.8 V, I_{OUT} = 300 mA T_A = 25 °C ⁽⁴⁾ V_{IN} = 1.5 V, I_{OUT} = 100 mA T_A = 25 °C			105			
					116			
R _{DSC}	Output Discharge Resistance	V _{EN} = Low, I _{FORCE} = 10 mA, GL	V _{EN} = Low, I _{FORCE} = 10 mA, GLF1201H				Ω	
V _{IH}	EN Input Logic High Voltage	V _{IN} = 1.5 V to 5.5 V		1.2			V	



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V_{IL}	EN Input Logic Low Voltage	V _{IN} = 1.5 V to 5.5 V		0.4	V
Ren	EN Internal Resistance	Internal Pull-down Resistance:	10		ΜΩ
I _{EN}	EN Current	V _{EN} = 5.5 V	0.5		μA
V _{RCB_TH}	RCB Protection Threshold Voltage	Vout – Vin	35		mV
V _{RCB_RL}	RCB Protection Release Voltage	V _{IN} - V _{OUT}	30		mV
Switching	g Characteristics ^(2, 3)				
t _{dON}	Turn-On Delay	D 450 0 0 0 4 v5	450		
t _R	V _{OUT} Rise Time	R_L = 150 Ω, C_{OUT} = 0.1 μF	600		
t _{dOFF}	Turn-Off Delay (4)	D = 450 O C = 0.4 vF : OLE420011	17]
t _F	V _{OUT} Fall Time (4)	R_L = 150 Ω, C_{OUT} = 0.1 μF : GLF1200H	27		μs
t _{dOFF}	Turn-Off Delay (4)	D = 450 O C = 0.4 vF : OL5420411	17		
t _F	V _{OUT} Fall Time (3), (4)	R_L = 150 Ω, C_{OUT} = 0.1 μF : GLF1201H	12		1

Notes:

- IQ does not include the enable pull down current (IEN) through the pull-down resistor REN.
- $t_{ON} = t_{dON} + t_{R}, t_{OFF} = t_{dOFF} + t_{F}$
- Output discharge path is enabled during off.
- 4. By design; characterized, not production tested.

TIMING DIAGRAM

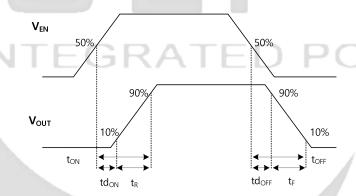
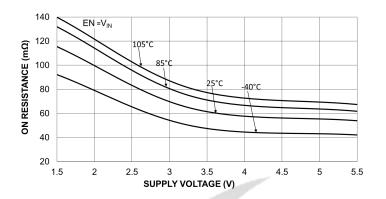


Figure 3. Timing Diagram



Nano Current Power IoSmart™ Switch with TRCB

TYPICAL PERFORMANCE CHARACTERISTICS



160 EN = V_{IN} ON RESISTANCE (mΩ) 140 120 100 80 V_{IN}=3.3V 60 40 20 -15 35 60 85 -40 110 T_J, JUNCTION TEMPERATURE (°C)

Figure 4. On-Resistance vs. Supply Voltage

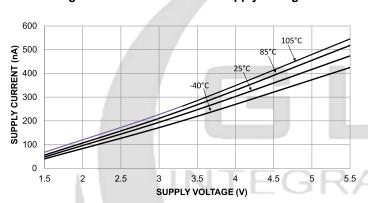


Figure 5. On-Resistance vs. Temperature

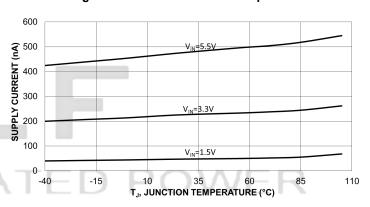


Figure 6. Quiescent Current vs. Supply Voltage

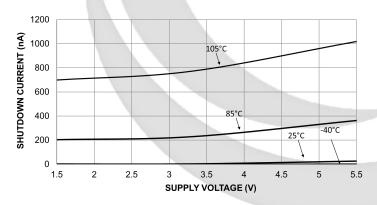


Figure 7. Quiescent Current vs. Temperature

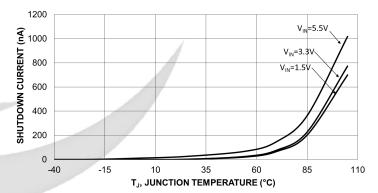


Figure 8. Shutdown Current vs. Supply Voltage

Figure 9. Shutdown Current vs. Temperature

Nano Current Power IoSmart™ Switch with TRCB

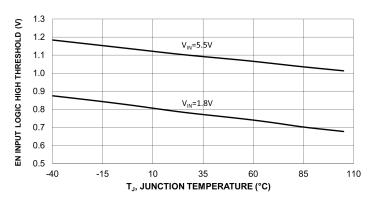


Figure 10. EN Input Logic High Threshold Vs. Temperature

Figure 11. EN Input Logic Low Threshold Vs. Temperature

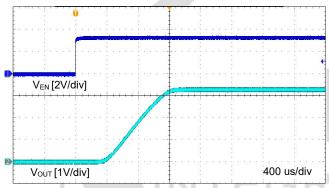


Figure 12. Turn-On Response, GLF1200H V_{IN} =3.3 V, C_{IN} =0.1 μ F, C_{OUT} =0.1 μ F, R_L =150 Ω

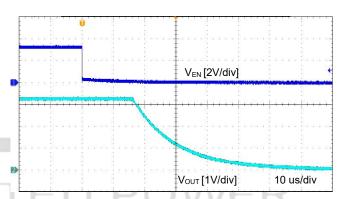


Figure 13. Turn-Off Response, GLF1200H V_{IN} =3.3 V, C_{IN} =0.1 μ F, C_{OUT} =0.1 μ F, R_L =150 Ω

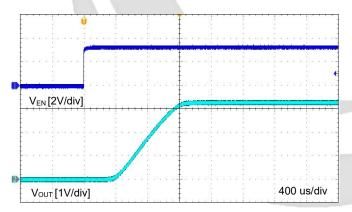


Figure 14. Turn-On Response, GLF1201H $V_{\text{IN}}\text{=}3.3 \text{ V, } C_{\text{IN}}\text{=}0.1 \text{ } \mu\text{F, } C_{\text{OUT}}\text{=}0.1 \text{ } \mu\text{F, } R_{\text{L}}\text{=}150 \text{ } \Omega$

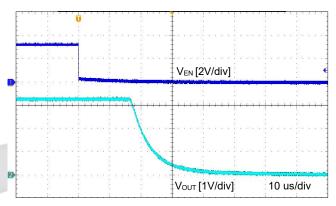
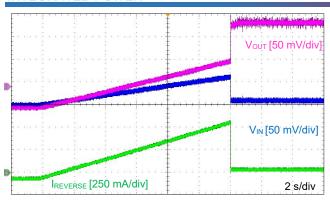


Figure 15. Turn-Off Response, GLF1201H V_{IN} =3.3 V, C_{IN} =0.1 μF , C_{OUT} =0.1 μF , R_L =150 Ω

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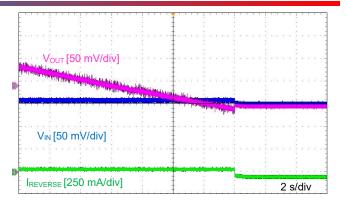


Figure 16. Reverse Current Blocking Threshold

Figure 17. Reverse Current Blocking Release

 $V_{\text{IN}} = 3.3 \text{ V}, V_{\text{OUT}} = \text{Up to } 3.4 \text{ V in } C_{\text{IN}} = 0.1 \text{ } \mu\text{F}, C_{\text{OUT}} = 0.1 \text{ } \mu\text{F}, R_{\text{L}} = 150 \text{ } \Omega$ $V_{\text{IN}} = 3.3 \text{ V}, V_{\text{OUT}} = \text{Down to } 3.2 \text{ V}, C_{\text{IN}} = 0.1 \text{ } \mu\text{F}, C_{\text{OUT}} = 0.1 \text{ } \mu\text{F}, R_{\text{L}} = 150 \text{ } \Omega$

APPLICATION INFORMATION

The GLF1200H / GLF1201H is an integrated 2 A, ultra-efficient I_QSmartTM load switch devices with a fixed slew rate control to limit the inrush current during turn on. Each device is capable of operating over a wide input voltage range from 1.5 V to 5.5 V with very low on-resistance to reduce conduction loss. In the off state, these devices consume very low leakage current to avoid unwanted standby current and save limited input power. The GLF1200H / GLF1201H is characterized for operation in the temperature range from -40 °C to 105 °C.

Input and Output Capacitor

A minimum 0.1 μ F input capacitor is recommended to be placed close to the V_{IN} pin to reduce the voltage drop on the input power rail caused by transient inrush current at start-up. A higher input capacitor value can be used to further attenuate the input voltage drop. Also, a minimum 0.1 μ F output capacitor is recommended to minimize voltage undershoot on the output pin during the transition when the switch is turned off. Undershoot can be caused by parasitic inductance from board traces or intentional load inductances. If load inductances do exist, use of an output capacitor can improve output voltage stability and system reliability. The C_{OUT} capacitor should be placed close to the VOUT and GND pins.

EN pin

The GLF1200H / GLF1201H can be activated by forcing EN pin high level. Note that the EN pin has an internal pull-down resistor to help pull the main switch to a known "off state" when no EN signal is applied from an external controller.

True Reverse Current Blocking

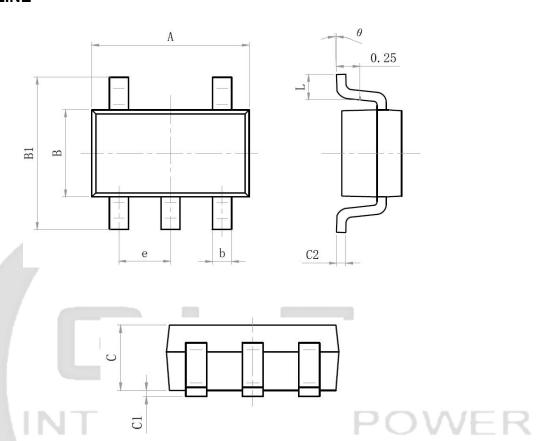
The GLF1200H / GLF1201H has a built-in reverse current blocking protection which always monitors the output voltage level regardless of the status of EN pin to check if it is greater than the input voltage. When the output voltage goes beyond the input voltage by the RCB protection threshold voltage (V_{RCV_TH}), the reverse current blocking function block turns off the switch. Note that some reverse current can occur until the V_{RCB} is triggered. The main switch will resume normal operation when the output voltage drops below the input source by the RCB protection release voltage (V_{RCV_RL}).

Output Discharge Function

The GLF1201H has an internal discharge N-channel FET switch on the VOUT pin. When EN signal turns the main power FET to an off state, the N-channel switch turns on to discharge an output capacitor quickly.

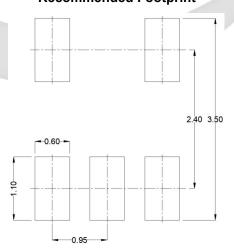


PACKAGE OUTLINE



Size Mark	Min(mm) Max(mm)		Size Mark	Min(mm)	Max(mm)
A	2.82	3.02	С	1.05	1. 15
е	0. 95 (BSC)		C1	0.03	0.15
b	0.28	0.45	C2	0.12	0. 23
В	1.50	1.70	L	0.35	0.55
B1	2.60	3.00	θ	0°	8°

Recommended Footprint

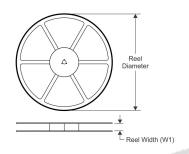


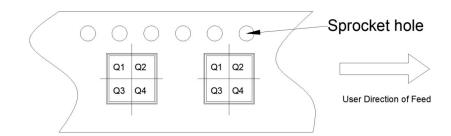


TAPE AND REEL INFORMATION

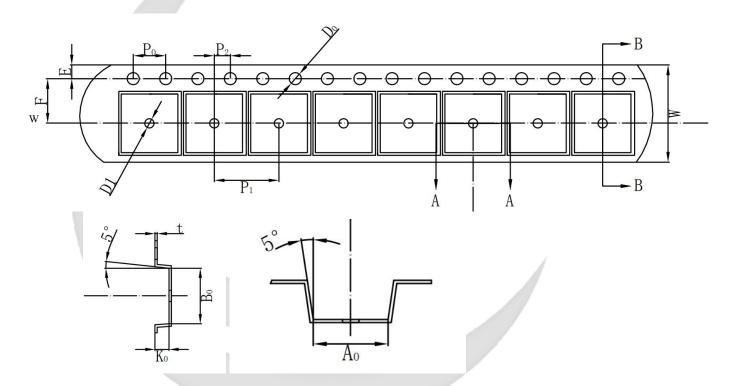
REEL DIMENSIONS

QUADRANT ASSIGNMENTS PIN 1 ORIENTATION TAPE





TAPE DIMENSIONS



Device	Package	Pins	SPQ	Reel Diameter (mm)	Reel Width W1	A0	В0	K0	P1	W	Pin1
GLF1200H-T1G7	SOT23-5	5	3000	178	9	3.25	3.30	1.38	4	8	Q3
GLF1201H-T1G7	SOT23-5	5	3000	178	9	3.25	3.30	1.38	4	8	Q3

Remark:

- A0: Dimension designed to accommodate the component width
- B0: Dimension designed to accommodate the component length
- C0: Dimension designed to accommodate the component thickness
- W: Overall width of the carrier tape
- P1: Pitch between successive cavity centers



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SPECIFICATION DEFINITIONS

Document Type	Meaning	Product Status			
Target Specification					
Preliminary Specification	· I change the specification at any time without warning or notification. A				
Product Specification	This document represents the anticipated production performance characteristics of the device.	Production			

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